



TSMC-03-375

April 30, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/798,178 03/11/04 |

Cheng-Ku Chen et al.

METHOD OF FORMING POLYSILICON GATE  
STRUCTURES WITH SPECIFIC EDGE  
PROFILES FOR OPTIMIZATION OF LDD  
OFFSET SPACING

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on May 4, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

Stephen B. Ackerman 5/4/04

U.S. Patent 6,514,830 to Fang et al., "Method of Manufacturing High Voltage Transistor with Modified Field Implant Mask," discloses a method of manufacturing a high voltage transistor exhibiting high gated diode breakdown voltage, low leakage and low body effect while avoiding an excessive number of costly masking steps.

U.S. Patent 6,350,639 to Yu et al., "Simplified Graded LDD Transistor Using Controlled Polysilicon Gate Profile," discusses a manufacturing method for Metal-Oxide-Semiconductors (MOS) which employ lightly doped drain (LDD) structures.

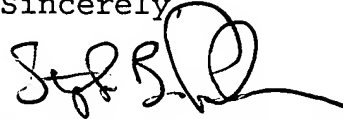
U.S. Patent 6,025,240 to Chan et al., "Method and System for Using a Spacer to Offset Implant Damage and Reduce Lateral Diffusion in Flash Memory Devices," discloses a system and method for providing a memory cell on a semiconductor.

U.S. Patent 6,294,432 to Lin et al., "Super Halo Implant Combined with Offset Spacer Process," discloses a method for forming a semiconductor structure by using super halo implant combined with offset spacer process.

TSMC-03-375

U.S. Patent 6,187,644 to Lin et al., "Method of Removing Oxynitride by Forming an Offset Spacer," discloses a method for forming a semiconductor device.

Sincerely

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman", with a large, stylized "S" and "A" and a long horizontal flourish extending to the right.

Stephen B. Ackerman,  
Reg. No. 37761

Form PTO-1449

# INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

MAY 06 2004

Docket Number (Optional)

TSMC-03-375

Application Number

10/798,178

Applicant

Cheng-Ku Chan et al.

Filing Date

03/11/04

Group Art Unit

## UNITED STATES PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	TITLE	CLASS	SUBCLASS	PLUNG DATE IF APPROPRIATE
	6514830	2/4/03	Fang et al.	438	302	1/11/02
	6350639	2/26/02	Yu et al.	438	199	4/10/01
	6025240	2/15/00	Chan et al.	438	303	12/18/97
	6187644	2/13/01	Lin et al.	438	303	9/8/99
	6294432	9/25/01	Lin et al.	438	301	12/20/99

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Portmox Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.